Kevin Jones

List of Publications by Year in Descending Order

104 papers	943 citations	17 h-index	27 g-index
106 ext. papers	1,025 ext. citations	3 avg, IF	3.61 L-index

#	Paper	IF	Citations
104	A new planar defect in SiGe nanopillars. *Microscopy and Microanalysis*, **2021**, 27, 1948-1949	0.5	
103	Wet-chemical etching of FIB lift-out TEM lamellae for damage-free analysis of 3-D nanostructures. *Ultramicroscopy*, **2020**, 216, 113049	3.1	2
102	Dissolution of antiphase domain boundaries in GaAs on Si(001) via post-growth annealing. *Journal of Materials Science*, **2019**, 54, 7028-7034	4.3	4
101	The Defect Formation Mechanism Associated with Low Dose Implants into Si Fin Structures **2018**,		1
100	Defect evolution in ultralow energy, high dose helium implants of silicon performed at elevated temperatures. *Journal of Applied Physics*, **2018**, 124, 165708	2.5	0
99	Lateral Ge Diffusion During Oxidation of Si/SiGe Fins. *Nano Letters*, **2017**, 17, 2159-2164	11.5	4
98	Quantification of germanium-induced suppression of interstitial injection during oxidation of silicon. *Journal of Materials Science*, **2017**, 52, 10387-10392	4.3	0
97	Use of a buried loop layer as a detector of interstitial flux during oxidation of SiGe heterostructures. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2017**, 35, 021101	2.9	2
96	Deposition, characterization and gas sensors application of RF magnetron-sputtered terbium-doped ZnO films. *Journal of Materials Science*, **2017**, 52, 8502-8517	4.3	25
95	Deactivation of electrically supersaturated Te-doped InGaAs grown by MOCVD. *Journal of Materials Science*, **2017**, 52, 10879-10885	4.3	1
94	Modulating the resistivity of MoS2 through low energy phosphorus plasma implantation. *Applied Physics Letters*, **2017**, 110, 262102	3.4	12
93	Quantitative correlation of interfacial contamination and antiphase domain boundary density in GaAs on Si(100). *Journal of Materials Science*, **2016**, 51, 449-456	4.3	6
92	Fermi-Level Effects on Extended Defect Evolution in Si+ and P+ Implanted In0.53Ga0.47As. *ECS Journal of Solid State Science and Technology*, **2016**, 5, P3073-P3077	2	3
91	Cycling performance and morphological evolution of pulsed laser-deposited FeF2 thin film cathodes for Li-ion batteries. *Journal of Materials Science*, **2015**, 50, 5174-5182	4.3	14
90	Lattice kinetic Monte Carlo modeling of germanium solid phase epitaxial growth. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2014**, 11, 93-96		1
89	Activation and defect dissolution of non-amorphizing, elevated temperature Si+ implants into In0.53Ga0.47As **2014**,		1
88	Field-induced defect morphology in Ni-gate AlGaN/GaN high electron mobility transistors. *Applied Physics Letters*, **2013**, 103, 023503	3.4	9

87	Maximizing electrical activation of ion-implanted Si in In0.53Ga0.47As. *Applied Physics Letters*, **2013**, 103, 232102	3.4	13
86	Substrate orientation dependence on the solid phase epitaxial growth rate of Ge. *Journal of Applied Physics*, **2013**, 113, 033505	2.5	11
85	Nanostructured ion beam-modified Ge films for high capacity Li ion battery anodes. *Applied Physics Letters*, **2012**, 100, 083111	3.4	79
84	Role of nucleation sites on the formation of nanoporous Ge. *Applied Physics Letters*, **2012**, 101, 131907	3.4	11
83	B segregation to grain boundaries and diffusion in polycrystalline Si with flash annealing. *Journal of Applied Physics*, **2012**, 111, 044508	2.5	11
82	Activation and thermal stability of ultra-shallow B+-implants in Ge. *Journal of Applied Physics*, **2012**, 112, 123525	2.5	3
81	Characterization of the gate oxide of an AlGaN/GaN high electron mobility transistor. *Applied Physics Letters*, **2011**, 98, 122103	3.4	30
80	Reverse gate bias-induced degradation of AlGaN/GaN high electron mobility transistors. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2010**, 28, 1044-1047	1.3	19
79	Modeling two-dimensional solid-phase epitaxial regrowth using level set methods. *Journal of Applied Physics*, **2009**, 105, 053701	2.5	18
78	Stressed multidirectional solid-phase epitaxial growth of Si. *Journal of Applied Physics*, **2009**, 105, 081101	2.5	36
77	Amorphization and graphitization of single-crystal diamond □A transmission electron microscopy study. *Diamond and Related Materials*, **2009**, 18, 1353-1359	3.5	62
76	Dopant-stress synergy in Si solid-phase epitaxy. *Applied Physics Letters*, **2008**, 92, 232110	3.4	13
75	Effect of low Ge content on B diffusion in amorphous SiGe alloys. *Journal of Vacuum Science & Technology B*, **2008**, 26, 333		2
74	Effect of carbon codoping on boron diffusion in amorphous silicon. *Applied Physics Letters*, **2008**, 93, 072107	3.4	5
73	Boron diffusion in amorphous silicon-germanium alloys. *Applied Physics Letters*, **2008**, 92, 172108	3.4	3
72	Characterization of Lanthanum Zirconate Formation at the A-Site-Deficient Strontium-Doped Lanthanum Manganite Cathode/Yttrium-Stabilized Zirconia Electrolyte Interface of Solid Oxide Fuel Cells. *Journal of the American Ceramic Society*, **2008**, 91, 2670-2675	3.8	20
71	Effect of uniaxial stress on solid phase epitaxy in patterned Si wafers. *Applied Physics Letters*, **2006**, 89, 082107	3.4	19
70	Using Quantitative TEM Analysis of Implant Damage to Study Surface Recombination Velocity in Silicon. *Materials Research Society Symposia Proceedings*, **2006**, 913, 1		

69	The effect of preamorphization energy on ultrashallow junction formation following ultrahigh-temperature annealing of ion-implanted silicon. *Journal of Applied Physics*, **2005**, 97, 044501	2.5	6
68	Solid Phase Recrystallization and Strain Relaxation in Ion-Implanted Strained Si on SiGe Heterostructures. *Materials Research Society Symposia Proceedings*, **2005**, 864, 4281		7
67	Epitaxial growth on gas cluster ion-beam processed GaSb substrates using molecular-beam epitaxy. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **2004**, 22, 1455		5
66	Impact of the end of range damage from low energy Ge preamorphizing implants on the thermal stability of shallow boron profiles. *Journal of Applied Physics*, **2004**, 96, 4939-4944	2.5	2
65	Concentration Dependence of Boron-Interstitial Cluster (BIC) Formation in Silicon-on-Insulator (SOI). *Materials Research Society Symposia Proceedings*, **2004**, 810, 357		
64	Gas-cluster ion-beam smoothing of chemo-mechanical-polish processed GaSb(100) substrates. *Journal of Electronic Materials*, **2003**, 32, 842-848	1.9	10
63	Electrical and Structural Characterization of Boron Implanted Silicon Following Laser Thermal Processing. *Materials Research Society Symposia Proceedings*, **2002**, 717, 1		2
62	Effect of Fluorine on the Diffusion of Boron in Amorphous Silicon. *Materials Research Society Symposia Proceedings*, **2002**, 717, 1		13
61	Varying implant dose rate for defect reduction in laser thermal processing. *Materials Science in Semiconductor Processing*, **2001**, 4, 339-343	4.3	3
60	Surface processing with gas-cluster ions to improve giant magnetoresistance films. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2001**, 19, 1207-1212	2.9	14
59	Influence of Arsenic Clustering and Precipitation on the Interstitial and Vacancy Concentration in Silicon. *Materials Research Society Symposia Proceedings*, **2001**, 669, 1		
58	Boron Solubility Limits Following Low Temperature Solid Phase Epitaxial Regrowth. *Materials Research Society Symposia Proceedings*, **2001**, 669, 1		10
57	Modeling of Dopant Defect Interactions. *Materials Research Society Symposia Proceedings*, **2001**, 669, 1		
56	Junction Depth Reduction of ion Implanted Boron in Silicon Through Fluorine ion Implantation. *Materials Research Society Symposia Proceedings*, **2000**, 610, 421		4
55	The Effect of Impurities on Diffusion and Activation of ion Implanted Boron in Silicon. *Materials Research Society Symposia Proceedings*, **2000**, 610, 581		3
54	Reaction of Excess Silicon Interstitals in the Presence of Arsenic and Germanium. *Materials Research Society Symposia Proceedings*, **2000**, 610, 841		
53	Phosphorus / Silicon Interstitial Annealing After Ion Implantation. *Materials Research Society Symposia Proceedings*, **2000**, 610, 661		1
52	Effect of the end-of-range loop layer depth on the evolution of {311} defects. *Applied Physics Letters*, **1999**, 74, 700-702	3.4	12

51	Effects of Co-Dopants on the Microstrucutre and El Properties of the ZnS:Mn Luminescence Materials. *Materials Research Society Symposia Proceedings*, **1999**, 560, 21		1
50	Effect of Extended Defects on the Enhanced Diffusion of Phosphorus Implanted Silicon. *Materials Research Society Symposia Proceedings*, **1999**, 568, 199		3
49	Capture of vacancies by extrinsic dislocation loops in silicon. *Applied Physics Letters*, **1998**, 72, 67-69	3.4	4
48	Interdiffusion Behavior of Si/Si1-xGex Layers in Inert and Oxidizing Ambients. *Materials Research Society Symposia Proceedings*, **1998**, 532, 119		3
47	Effect of the End of Range Loop Layer Depth on the Evolution of {311} Defects. *Materials Research Society Symposia Proceedings*, **1998**, 532, 61		
46	The effect of boron implant energy on transient enhanced diffusion in silicon. *Journal of Applied Physics*, **1997**, 81, 1656-1660	2.5	21
45	The Role of Vacancies and Interstitials in Transient Enhanced Diffusion of Arsenic Implanted into Silicon. *Materials Research Society Symposia Proceedings*, **1997**, 469, 315		5
44	Effect of End-of-Range Defects, Arsenic Clustering and Precipitation on Transient Enhanced Diffusion in As+ Implanted Si. *Materials Research Society Symposia Proceedings*, **1997**, 469, 401		3
43	Effect of Implant Energy on Silicon Defect Evolution. *Materials Research Society Symposia Proceedings*, **1997**, 469, 283		2
42	The Role of Gallium Sulfide in Srs:Ce Grain Growth. *Microscopy and Microanalysis*, **1997**, 3, 987-988	0.5	
41	The effect of dose rate and implant temperature on transient enhanced diffusion in boron implanted silicon. *Journal of Electronic Materials*, **1997**, 26, 1361-1364	1.9	5
40	An Investigation of Vacancy Population During Arsenic Activation in Silicon. *Materials Research Society Symposia Proceedings*, **1996**, 442, 151		
39	Effect of Energy and Dose on Transient-Enhanced Diffusion and Defect Microstructure in Low Energy High Dose As+ Implanted Si. *Materials Research Society Symposia Proceedings*, **1996**, 438, 21		
38	Effect of Energy and Dose on Transient-Enhanced Diffusion and Defect Microstructure in Low Energy High Dose As+ Implanted Si. *Materials Research Society Symposia Proceedings*, **1996**, 439, 29		
37	Enhanced Dissolution of Extrinsic Dislocation Loops in Silicon Annealed in NH3. *Materials Research Society Symposia Proceedings*, **1996**, 442, 157		
36	Effect of Oxygen Dose Variation on the Simox Microstructure. *Materials Research Society Symposia Proceedings*, **1996**, 446, 207		
35	Dose-rate effects in silicon-implanted gallium arsenide from low to high doses. *Journal of Electronic Materials*, **1996**, 25, 107-111	1.9	2
34	The effects of processing conditions on the density and microstructure of hot-pressed silicon powder. *Journal of Materials Science*, **1996**, 31, 4985-4990	4.3	9

33	Growth of InxGa1−xN and InxAl1−xN on GaAs metalorganic molecular beam epitaxy. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **1995**, 13, 716-718	2.9	22
32	Dislocations in lattice-mismatched wide-gap II-VI/GaAs heterostructures as laser light scatterers: Experiment and theory. *Journal of Applied Physics*, **1995**, 78, 1203-1209	2.5	14
31	Electrical and structural properties of InxGa1−xN on GaAs. *Applied Physics Letters*, **1995**, 66, 1632-1634	3.4	39
30	Type II Dislocation Loops and their Effect on Strain in Ion Implanted Silicon as Studied by High Resolution X-ray Diffraction. *Materials Research Society Symposia Proceedings*, **1995**, 378, 635		1
29	Effects of Arsenic Deactivation on Arsenic-Implant Induced Enhanced Diffusion in Silicon. *Materials Research Society Symposia Proceedings*, **1995**, 396, 167		
28	Titanium Silicidation Induced Point Defects in Si. *Materials Research Society Symposia Proceedings*, **1995**, 402, 143		
27	Blue And Yellow Light Emitting Phosphors For Thin Film Electroluminescent Displays. *Materials Research Society Symposia Proceedings*, **1994**, 345, 289		1
26	Effect of implant temperature on dopant diffusion and defect morphology for Si implanted GaAs. *Journal of Applied Physics*, **1994**, 76, 4571-4575	2.5	10
25	The Effect of Titanium Silicidation on Type II End-of-Range Dislocation Loops. *Materials Research Society Symposia Proceedings*, **1994**, 337, 469		
24	Thermal Expansion Behavior of ZnSe and ZnS0.03Se0.97 Epilayers on GaAs at Temperatures in the Range, 25°C - 250°C. *Materials Research Society Symposia Proceedings*, **1994**, 340, 475		
23	A Study of Loop Evolution During Inert Ambient Annealing and Reaction Between Point Defects and Dislocation Loops During Oxidation of Silicon. *Materials Research Society Symposia Proceedings*, **1994**, 354, 293		
22	Sputtering Induced Changes in Defect Morphology and Dopant Diffusion for Si Implanted GaAs: Influence of Ion Energy and Implant Temperature. *Materials Research Society Symposia Proceedings*, **1994**, 354, 337		4
21	Carrier Confinement Effects in Epitaxial Silicon Quantum Wells Prepared by MOCVD. *Materials Research Society Symposia Proceedings*, **1994**, 358, 987		
20	Kinetics of solid phase epitaxial regrowth in amorphized Si0.88Ge0.12 measured by time-resolved reflectivity. *Applied Physics Letters*, **1993**, 62, 501-503	3.4	44
19	A study of point defect detectors created by Si and Ge implantation. *Journal of Applied Physics*, **1993**, 73, 955-960	2.5	27
18	Use of type II (end of range) damage as "detectors" for quantifying interstitial fluxes in ion-implanted silicon. *Journal of Applied Physics*, **1993**, 73, 4815-4819	2.5	44
17	The electron microscopy of post-growth induced defects of ZnSe/GaAs epilayers. *Journal of Electronic Materials*, **1993**, 22, 239-245	1.9	
16	Characterization of ZnS Layers Grown by MOCVD for Thin Film Electroluminescence (TFEL) Devices. *Materials Research Society Symposia Proceedings*, **1992**, 242, 215		3

15	Point Defect Detector Studies of Ge+ Implanted Silicon Upon Oxidation. *Materials Research Society Symposia Proceedings*, **1992**, 262, 253		0
14	Time-Resolved Reflectivity Study of Solid-Phase Epitaxial Regrowth in Relaxed and Strained Si1-xGex Epilayers. *Materials Research Society Symposia Proceedings*, **1992**, 281, 479		
13	Strain Relief and Defect Formation in High Dose Oxygen Implanted Silicon. *Materials Research Society Symposia Proceedings*, **1991**, 235, 103		13
12	Solid Phase Epitaxial Regrowth of Implantation Amorphized Si0.7Ge0.3 Grown on (100) Silicon. *Materials Research Society Symposia Proceedings*, **1991**, 235, 57		
11	Point Defect Detector Studies of Oxidized Silicon. *Materials Research Society Symposia Proceedings*, **1991**, 238, 101		1
10	Correlation of Dislocation Loop Formation and Time Dependent Diffusion of Implanted P-Type Dopants in Gallium Arsenide. *Materials Research Society Symposia Proceedings*, **1991**, 240, 715		2
9	The effect of implant energy, dose, and dynamic annealing on end-of-range damage in Ge+-implanted silicon. *Journal of Applied Physics*, **1991**, 69, 2931-2937	2.5	66
8	GaAs/AlGaAs quantum well and modulation-doped heterostructures grown by organometallic vapor phase epitaxy using trimethylamine alane. *Applied Physics Letters*, **1991**, 59, 1975-1977	3.4	12
7	High-purity InP grown on Si by organometallic vapor phase epitaxy. *Applied Physics Letters*, **1991**, 58, 1554-1556	3.4	7
6	Amorphization of elemental and compound semiconductors upon ion implantation. *Journal of Materials Research*, **1991**, 6, 1048-1054	2.5	33
5	Raman Studies of Znse Lattice Damage and Recovery Due to N Implantation and Annealing. *Materials Research Society Symposia Proceedings*, **1990**, 209, 457		
4	Observation of the Wurtzite Phase in OMVPE Grown ZnSe/GaAs: Effect on Implantation and Rapid Thermal Annealing. *Materials Research Society Symposia Proceedings*, **1989**, 147, 339		1
3	Low-Energy Implantation of Si and Sn into GaAs. *Materials Research Society Symposia Proceedings*, **1989**, 157, 677		2
2	The Effect of Implant Species on the Stability of Ion Implantation Damage. *Materials Research Society Symposia Proceedings*, **1988**, 100, 277		7
1	Ion Impiantation Doping of Siox with 31P and 69Ga. *Materials Research Society Symposia Proceedings*, **1988**, 128, 617		